

A suggestion for spin-position gates in mobile electron-based quantum information processing

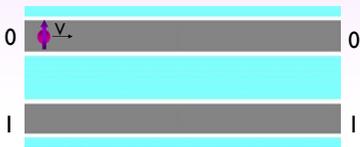
S. Alipour¹, A. T. Rezakhani², and M. Esmaelzadeh³

¹Sharif University of Technology ²University of Calgary ³Iran University of Science and Technology

We investigate implementation of quantum computation by using spin and position degrees of freedom of electrons moving in the quantum wires. Such quantum wires can be realized in a two-dimensional electron gas, where electrons are assumed to move uniformly in either of two possible rails. We show, how one can combine two previous methods for performing quantum computation.

The qubits in the system:

1. Spin qubits [1]



A two-qubit state: $|\psi\rangle = |\sigma, k\rangle = |0, 0\rangle$

Spin degree of freedom Position degree of freedom

$$\begin{cases} |\uparrow\rangle = |0\rangle \\ |\downarrow\rangle = |1\rangle \end{cases} \quad \begin{cases} k=0 & \text{electron in the top wire} \\ k=1 & \text{electron in the bottom wire} \end{cases}$$

2. Dual-rail qubits [2]

Single qubit gates:

1. Spin rotation gates [1]

We use Rashba Hamiltonian for spin degree of freedom. Electron moves in an electric field: $\vec{E} = E\hat{n}$

Electron sees a magnetic field in its rest reference frame: $\vec{B} \sim \vec{V} \times \vec{E}$



Rashba Hamiltonian: $H_R = \alpha(\hat{n} \times \vec{k}) \cdot \vec{\sigma}$

$$\hbar \vec{k} = m^* \vec{v} \quad \alpha = \frac{e \hbar}{2(m^* c)^2} E \quad \text{and} \quad \vec{\sigma} = (\sigma_x, \sigma_y, \sigma_z) \quad \text{Pauli matrices}$$

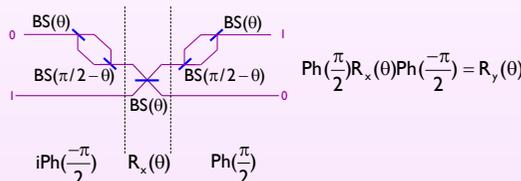
m^* : Electron's effective mass, l : the length of the Rashba region

Single-spin rotation gate: $e^{-iH_R l / \hbar} = e^{-i\alpha l (\hat{n} \times \hat{v}) \cdot \vec{\sigma} / \hbar^2}$

2. Position gates [3]

$U_{BS} : |k\rangle \rightarrow \cos \theta |k\rangle + i \sin \theta |1-k\rangle$

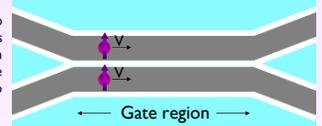
$U_{BS} = R_x(\theta) = \begin{pmatrix} \cos \theta & i \sin \theta \\ i \sin \theta & \cos \theta \end{pmatrix}$ Probability of transmission: $|\cos \theta|^2$
Probability of Reflection: $|\sin \theta|^2$



Two-qubit gates:

1. A two-qubit gate for spin qubits: SWAP [1]

Two quantum wires are more closer to each other in the gate region. In this region electrons can interact with each other and we can represent the effective Hamiltonian between two electrons by Heisenberg Hamiltonian.



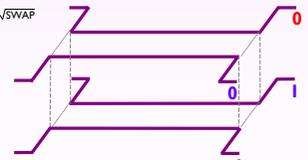
$$H_{\text{exchange}} = J(t) \vec{S}_1 \cdot \vec{S}_2 \rightarrow U_{\text{exchange}} = e^{i\beta/4} e^{-i\beta/2 U_{\text{SWAP}}}$$

in which $\vec{S} = \frac{1}{2} \vec{\sigma}$, $\beta = \frac{1}{\hbar} \int_{t_1}^{t_2} J(t) dt$ and $U_{\text{SWAP}} = \frac{1}{2} (1 + \vec{\sigma}_1 \cdot \vec{\sigma}_2)$

$$U_{\text{exchange}}(\beta) = e^{i\beta/4} (\cos \frac{\beta}{2} I - i \sin \frac{\beta}{2} U_{\text{SWAP}}) \rightarrow \text{If } \beta = \frac{\pi}{2}$$

$$\rightarrow U_{\text{exchange}}(\frac{\pi}{2}) = e^{-i\frac{\pi}{8}} U_{\text{SWAP}}$$

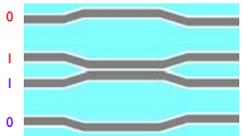
$$U = I_{k_1 k_2} \otimes \sqrt{\text{SWAP}}_{\sigma_1 \sigma_2}$$



Each electron is permitted to move in a dual-rail with differentiated color, without tunneling between two wires.

2. A two-qubit gate for dual-rail qubits: S(pi)

$$S(\pi) = \begin{pmatrix} 1 & 0 & 0 & 0 \\ 0 & 1 & 0 & 0 \\ 0 & 0 & i & 0 \\ 0 & 0 & 0 & e^{i\pi} \end{pmatrix}$$



$$H = (J(t) \vec{S}_1 \cdot \vec{S}_2) - H_0 \delta_{k_1, l} \delta_{k_2, l} + H_0 \quad \text{and} \quad H_0 = H_0^{(1)} + H_0^{(2)} \quad [3]$$

We can construct controlled-phase shifter, by using eight successive Coulomb couplers with $\beta = \pi/2$.

If both electrons move in the rail-1 ($k_1 = k_2 = 1$), then we have: since $\sqrt{\text{SWAP}}^8 = I$ then the status of spin qubits will not change.

$$U = (U_{\text{exchange}}(\frac{\pi}{2}))^8 |\sigma_1, l; \sigma_2, l\rangle \langle \sigma_1, l; \sigma_2, l| = e^{-i\pi} |\sigma_1, l; \sigma_2, l\rangle \langle \sigma_1, l; \sigma_2, l| \quad [3]$$

3. A two-qubit gate for spin and dual-rail qubits: CNOT

$$|\psi\rangle = \alpha |0, 0\rangle_{\sigma, k} + \beta |1, 0\rangle_{\sigma, k}$$

The local magnetic field between two wires causes an Aharonov-Bohm phase difference between top and bottom branches. Because the electric field in Rashba region creates a magnetic field toward z-axis this only gives different phases to electrons with spin up and down without rotating them.

By controlling magnetic field and the Rashba region we can tune interference between electron waves in top and bottom rails such that electrons with different spins separate in the output of the apparatus.

$$U_{\text{PBS}} : |\uparrow, 0\rangle \rightarrow |\uparrow, 0\rangle, |\downarrow, 0\rangle \rightarrow |i\downarrow, 1\rangle, |\uparrow, 1\rangle \rightarrow -|\uparrow, 1\rangle, |\downarrow, 1\rangle \rightarrow |i\downarrow, 0\rangle \quad [4]$$

$$\text{CNOT} = (I_{\sigma} \otimes \text{Ph}(\frac{-\pi}{2})) U_{\text{PBS}} (I_{\sigma} \otimes \text{Ph}(\frac{-\pi}{2})) \quad [3]$$

References :

- [1] A. E. Popescu and R. Ionicioiu, Phys. Rev. B **69**, 245422 (2004).
- [2] R. Ionicioiu, G. Amarantunga, and F. Udrea, quant-ph/0011051
- [3] S. Alipour, MS Thesis (IUST, 2005).
- [4] R. Ionicioiu and I. D'Amico, Semicond. Sci. Technol. **19**, S418 (2004)